課題番号 : F-14-UT-0142

利用形態:機器利用

利用課題名(日本語) :シリコンフォトニクスのための MIDEX(中程度屈折率差系)光学系の研究

Program Title (English) : Mid-Refractive Index Contrast Optics for Si Photonics

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# 1. 概要(Summary)

I aim to develop an integrated photonic circuit platform on bulk Silicon wafer based on mid-refractive index contrast optics for Si Photonics for the future dense wavelength-division multiplexing system. This research project will study electro-optical properties of the CMOS compatible material of GeSi, SiN,  $SiO_xN_y$ , and  $SiO_2$  on bulk Si wafer for future telecom systems.

## 2. 実験(Experimental)

I have been using several machines at the Takeda cleanroom during 2014-2015. I enormously profit from the use of ADVANTEST F5112 e-beam lithography, allowing me to obtain large and highly-resolute structures rapidly. Equally important, I use the PVD sputtering machine, which allows me to study Silicon nitride materials deposited at low-temperature for wavelength -division multiplexing system. I also employ CE-300I ICP-RIE to pattern the device. During all the process, scanning electron microscope (SEM) and optical microscope are widely used to observe the progress.

# 3. 結果と考察(Results and Discussion)

I have finished the process development and fabrication of an array waveguide grating(AWG) using Takeda cleanroom facilities. The experiment and analysis are under investigation.

#### 4. その他・特記事項(Others)

The work is in close collaboration with the

University of Paris in France.

# 5. 論文·学会発表(Publication/Presentation)

- (1) P. Chaisakul et al., SPIE Photonics Asia, 92770E-92770E-7, Beijing China, 9-11 Oct 2014
- (2) P. Chaisakul et al., Japanese Society of Applied Physics, 18a-A18-1, Hokkaido Japan, 17-20 Sep 2014
- (3) P. Chaisakul et al., The 7th Forum on the Science and Technology of Silicon Materials, PT07-1, pp.157, Hamamatsu, Japan, 19-22 October 2014

## 6. 関連特許(Patent)

None